Group - D

- Explain DNL and INL in analog-to-digital converters. Is any ADC 6. (a) possessing a DNL is guaranteed to have a Missing Code? Justify vour answer.
  - (b) Explain the operation of a Flash ADC. Briefly discuss its accuracy issues.

(4+2) + (4+2) = 12

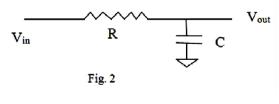
- 7. (a) Explain the operation of DAC architecture with R-2R ladder network.
  - Discuss the role of "Dummy Switch" in this architecture. (b)
  - (c) Design a 3-bit DAC using an R-2R architecture with R=1k $\Omega$ ,  $R_{f}=2 \text{ k}\Omega$  and  $V_{RFF}=5V$ . Assume that the resistances of the switches are negligible. Determine the value of itot for each digital input and the corresponding output voltage V<sub>out</sub>.

4 + 2 + 6 = 12

6 + 6 = 12

# Group - E

- 8. (a) Emulate the Resistor equivalent of a Parallel Switched capacitor circuit.
  - Using Switched capacitor techniques, implement the circuit shown in (b) the Fig. 2, so that the product of RC is 1mS, that is, the 3-dB frequency of |V<sub>out</sub>/V<sub>in</sub>| is 159Hz.



- 9. (a) Explain the operation of three stage ring oscillator.
  - (b) Analyse what happens if in the three stage ring  $A_0 \neq 2$ .
  - (c) Determine the maximum voltage swing of each stage of a three stage ring oscillator incorporating differential pair with resistive loads. 5 + 4 + 3 = 12

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## ANALOG VLSI IC DESIGN (VLSI 5201)

Time Allotted : 3 hrs

Full Marks: 70

Figures out of the right margin indicate full marks.

Candidates are required to answer Group A and any 5 (five) from Group B to E, taking at least one from each group.

### Candidates are required to give answer in their own words as far as practicable.

## Group – A (Multiple Choice Type Questions)

- 1. Choose the correct alternative for the following:  $10 \times 1 = 10$ 
  - (i) MOS device being symmetric
    - (a) doping concentration of source terminal should be higher compared to drain terminal
    - (b) source and drain terminals are interchangeable
    - (c) doping concentration of source terminal should be lesser compared to drain terminal
    - (d) source and drain terminals are not interchangeable.
  - The number of stages in a ring oscillator is determined by various (ii) requirements including (a) speed (b) power dissipation (d) all of the above. (c) noise immunity
  - In order to realize MOS device as a zero-offset switch, it should be (iii) operated in (a) deep triode region (b) triode region (c) either linear or saturation region

	(b) though the gibin
n	(d) saturation region.

- The frequency of the signal applied to the switched-capacitor circuit (iv) should satisfy the criteria (a)  $f_{signal} \ll f_{clock}$ (b)  $f_{signal} >> f_{clock}$ (c)  $f_{signal} = 2 f_{clock}$ (d)  $f_{clock} = 2 f_{signal}$
- The ENOB of a DAC is defined as (v) (a) (SNR <sub>actual</sub> – 1.76) /6.02 (b)  $(SNR_{max} - 1.76) / 6.02$ (c)  $(SNR_{actual} + 1.76) / 6.02$ (d)  $(SNR_{max} + 1.76) / 6.02$ .

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- (vi) The folded cascode op-amp has
  - (a) higher power dissipation and higher voltage gain than telescopic configuration
  - (b) lower power dissipation and higher voltage gain than telescopic configuration
  - (c) lower power dissipation and lower voltage gain than telescopic configuration
  - (d) higher power dissipation and lower voltage gain than telescopic configuration.
- (vii) The primary disadvantages of the switched capacitor circuits are
  - (a) necessity of the bandwidth of the signal being less than the clock frequency
  - (b) necessity of the bandwidth of the signal being greater than the clock frequency
  - (c) requirement of non overlapping clock
  - (d) both (a) & (c).
- (viii) Considering  $V_{REF} = 1V$ , as the digital word increases by 1 bit, the output of the ideal 3-bit DAC should jump by (a) 0.25V (b) 0.0625V (c) 0.33V (d) 0.125V.
- (ix) Practical current mirror circuits deviate from ideal behaviour due to
  (a) channel length modulation effect
  (b) threshold voltage offset between two transistors
  (c) imperfect geometrical matching
  - (d) all of the above.
- (x) An ideal differential amplifier should have CMRR
  (a) 0 < CMRR < 1</li>
  (b) one
  (c) infinite
  (d) zero.

# Group - B

- 2. (a) Draw and explain the high-frequency small-signal equivalent circuit of the MOSFET.
  - (b) Mention the advantages of differential operation over single-ended operation.
  - (c) Calculate the differential gain of a basic resistive load differential amplifier circuit.

5 + 2 + 5 = 12

3. (a) Briefly discuss the limitations of the MOS switch and also the methods adopted to reduce them.

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(b)

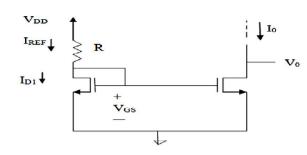


Fig. 1 In the circuit shown in Fig. 1 given  $V_{dd}$ =3V and using  $I_{REF}$ =100µA, it is required to design the above circuit to obtain an output current whose nominal value is 100µA. Find R if both the MOS are matched and have channel lengths of 1µm, channel widths of 10µm,  $V_t$ =0.7V and  $k_n'$ =200µA/V<sup>2</sup>. What is the lowest possible value of  $V_0$ ? Assuming that for this process technology the Early voltage  $V_A'$ =20V/µm, find the output resistance of the current source. Also find the change in output current resulting from a +1V change in  $V_0$ . **6**+6=12

## Group - C

- 4. (a) Distinguish between the time variance and non-linearity attribute of an RF circuit.
  - (b) A 900 MHz GSM transmitter delivers a power of 1watt to the antenna. By how much must the second harmonic of the signal be suppressed (filtered) so that it does not desensitize a 1.8GHz receiver having  $P_{1db}$ =-25 dBm? Assure that the receiver is 1m away and the 1.8GHz signal is attenuated by 10dB as it propagates across the distance.
  - (c) Discuss briefly the phenomenon of Cross Modulation. Suppose an interferer contains phase modulation but not amplitude modulation, does Cross Modulation occur in this case?

4 + 4 + 4 = 12

- 5. (a) Explain Skin Effect. Does "Current Crowding" effect influence inductance and capacitance of Spiral Geometries? Justify your answer.
  - (b) Estimate the power lost in the substrate using a distributed model of a spiral inductor.

(3 + 4) + 5 = 12

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